L Number	Hits	Search Text	DB	Time stamp
1	118	@ad<=20010104 and 'amorphous silicon' same 'metal' same 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:30
3	0	@ad<=20010104 and 'amorphous silicon' same 'metal' near 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:29
2	58	@ad<=20010104 and 'amorphous silicon' same 'metal' with 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:29
4	0	@ad<=20010104 and 'amorphous silicon' near 'metal' near 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:29
5	52	@ad<=20010104 and 'amorphous silicon' with 'metal' with 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:55
6	1	@ad<=20010104 and 'amorphous silicon' same 'sputtering' with 'metal' same 'simultaneously' same 'heating'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:45
7	1	@ad<=20010104 and 'amorphous silicon' same 'sputtering' with 'metal' and 'simultaneously' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:52
8	8	@ad<=20010104 and 'amorphous silicon' and 'sputtering' with 'nickel' and 'heating' with 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:52
9	0	@ad<=20010104 and 'sputtering' with 'nickel' same 'heating substrate' with 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:52
10	42	@ad<=20010104 and 'sputtering' with 'metal' and 'simultaneously' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:53
11	2	@ad<=20010104 and 'sputtering' with 'metal' same 'simultaneously' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:53
12	0	@ad<=20010104 and 'amorphous silicon' with 'metal' with 'heating substrate' same 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:55
13	0	@ad<=20010104 and 'amorphous silicon' with 'metal' same 'heating substrate' same 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:56
14	7	@ad<=20010104 and 'amorphous silicon' with 'metal' and 'heating substrate' same 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:14

15	7	@ad<=20010104 and 'amorphous silicon' with 'metal' and 'heating' adj1 'substrate' same 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:03
16	0	@ad<=20010104 and 'a-si' and 'sputter' near4 'metal' and 'heating substrate' same 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:15
17	0	@ad<=20010104 and 'a-si' and 'sputter' same 'metal' and 'heating' with 'substrate' same 'simultaneously'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:15
18	26	@ad<=20010104 and 'a-si' and 'sputter' same 'metal' and 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:26
21	195	@ad<=20010104 and 'sputter' same 'nickel' and 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:28
26	2	@ad<=20010104 and 'sputter' same 'nickel' with 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:28
27	71	@ad<=20010104 and 'amorphous silicon' same 'nickel' same 'heating' with 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 08:30
28	4	@ad<=20010104 and 'MILC' with 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 09:35
29	6	@ad<=20010104 and 'MILC' same 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 09:35
-	1192	@ad<=20010104 and 'heating substrate' and 'amorphous silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 13:46
-	943	((438/486) or (438/482)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:05
-	71	(((438/486) or (438/482)).CCLS.) and @ad<=20010104 and 'heating substrate' and 'amorphous silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:00
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'heating substrate' and 'amorphous silicon' and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:18
-	2	(((438/486) or (438/482)).CCLS.) and MILC and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:36

-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and MILC and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:06
-	0	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'while depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 07:25
-	181	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	109	(@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating') and 'depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	14	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'amorphous silicon' and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:10
-	303	(((438/486) or (438/482)).CCLS.) and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:37
-	52	(((438/486) or (438/482)).CCLS.) and 'low temperature' and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:37
-	0	@ad<=20010104 and heating adj1 substrate with depositing same metal and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:51
-	58	@ad<=20010104 and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 13:55
-	0	@ad<=20010104 and heating adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:54
-	0	@ad<=20010104 and heat adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:54
-	3	@ad<=20010104 and heat adj1 substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:56
-	74	@ad<=20010104 and heating adj1 substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:15

-	15	@ad<=20010104 and 'hot metallization'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:16
-	191	@ad<=20010104 and 'amorphous silicon' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:55
-	12	@ad<=20010104 and 'amorphous silicon' same 'heating substrate' same 'metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:40
-	3778	((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:42
-	54	(((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.) and @ad<=20010104 and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:56
-	2	"20020137310"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:55
-	447	@ad<=20010104 and low adj temperature adj crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:35
-	318928	(("257") or ("438")).CLAS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 13:59
-	124	(@ad<=20010104 and low adj temperature adj crystallization) and 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:13
-	1	("6524662").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:07
-	28	(@ad<=20010104 and low adj temperature adj crystallization) and heat adj substrate and 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:14
-	9	@ad<=20010104 and deposit adj nickel same 'heat' same 'substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:39
-	6	@ad<=20010104 and 'heated' with 'substrate' same deposit adj nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/11 14:40
-	62	@ad<=20010104 and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:26

-	3	("6524662").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:22
-	24	@ad<=20010104 and Joo-seung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:27
-	39	Joo-seung-ki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:27
-	2	("6097037").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 11:57
-	231	@ad<=20010104 and 'amorphous silicon' same 'nickel' same 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:02
-	53	@ad<=20010104 and 'amorphous silicon' with 'nickel' with 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:19
-	8	@ad<=20010104 and 'amorphous silicon' with 'nickel' with 'sputtering' with 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:22
-	222	@ad<=20010104 and 'sputtering' with 'temperature' same 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:22
-	100	@ad<=20010104 and 'sputtering' with 'temperature' with 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:27
-	5	@ad<=20010104 and 'nickel' with 'sputtering temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:49
-	0	@ad<=20010104 and 'nickel' with 'oxidation' adj1 'stable' with 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:48
-	6	@ad<=20010104 and 'nickel' with 'oxidation' adj1 'stable'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:48
-	11	@ad<=20010104 and 'nickel' same 'sputtering temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:55
-	93	@ad<=20010104 and 'nickel' same 'oxidation temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 12:56

-	31	@ad<=20010104 and 'nickel' with 'oxidation temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:02
-	72	@ad<=20010104 and 'nickel' with 'silicidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:02
-	27	@ad<=20010104 and 'nickel' adj1 'silicidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:04
-	26	@ad<=20010104 and 'nickel' adj1 'silicidation' and 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:04
-	17	@ad<=20010104 and 'nickel' adj1 'silicidation' same 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:15
-	153	@ad<=20010104 and 'nickel' same 'silicon' with 'crystallized' same 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:16
-	64	@ad<=20010104 and 'nickel' same 'silicon' with 'crystallized' with 'temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:16
-	2	("5614291").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 13:22
-	2	"20020137310"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/22 13:14
-	12	@ad<=20010104 and MILC and 'nickel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/23 09:34